

1.5V Drive Nch + Pch MOSFET

TT8M1

● Structure

Silicon N-channel MOSFET/
 Silicon P-channel MOSFET

● Features

- 1) Low on-resistance.
- 2) High power package (TSST8).
- 3) Low voltage drive (1.5V drive).

● Application

Switching

● Packaging specifications

Type	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	3000
TT8M1		○

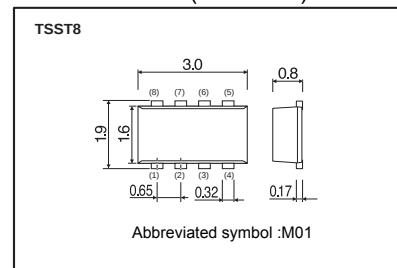
● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits		Unit
		Tr1 : N-ch	Tr2 : P-ch	
Drain-source voltage	V_{DSS}	20	-20	V
Gate-source voltage	V_{GSS}	±10	±10	V
Drain current	Continuous	I_D	±2.5	A
	Pulsed	I_{DP} *1	±10	A
Source current (Body Diode)	Continuous	I_S	0.8	A
	Pulsed	I_{sp} *1	10	A
Power dissipation	P_D *2	1.25		W / TOTAL
		1		W / ELEMENT
Channel temperature	T_{ch}	150		°C
Range of storage temperature	T_{stg}	-55 to +150		°C

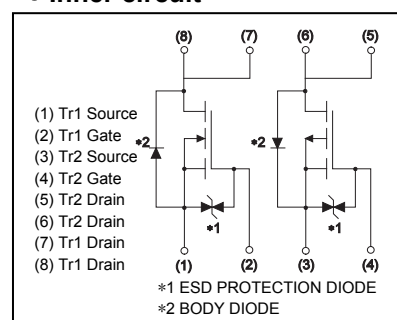
*1 $P_w \leq 10\text{W}$, Duty cycle $\leq 1\%$

*2 Mounted on a ceramic board.

● Dimensions (Unit : mm)



● Inner circuit



● **Electrical characteristics** (Ta = 25°C)

<Tr1(Nch)>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	± 10	μA	$V_{GS} = \pm 10V, V_{DS} = 0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	20	-	-	V	$I_D = 1mA, V_{GS} = 0V$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS} = 20V, V_{GS} = 0V$
Gate threshold voltage	$V_{GS(th)}$	0.3	-	1.0	V	$V_{DS} = 10V, I_D = 1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	-	52	72	m Ω	$I_D = 2.5A, V_{GS} = 4.5V$
		-	65	90		$I_D = 2.5A, V_{GS} = 2.5V$
		-	85	120		$I_D = 1.2A, V_{GS} = 1.8V$
		-	100	140		$I_D = 0.5A, V_{GS} = 1.5V$
Forward transfer admittance	$ Y_{fs} ^*$	2.7	-	-	S	$V_{DS} = 10V, I_D = 2.5A$
Input capacitance	C_{iss}	-	260	-	pF	$V_{DS} = 10V$
Output capacitance	C_{oss}	-	65	-	pF	$V_{GS} = 0V$
Reverse transfer capacitance	C_{rss}	-	35	-	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}^*$	-	9	-	ns	$I_D = 1.2A, V_{DD} = 10V$
Rise time	t_r^*	-	17	-	ns	$V_{GS} = 4.5V$
Turn-off delay time	$t_{d(off)}^*$	-	28	-	ns	$R_L = 8.3\Omega$
Fall time	t_f^*	-	17	-	ns	$R_G = 10\Omega$
Total gate charge	Q_g^*	-	3.6	-	nC	$I_D = 2.5A, V_{DD} = 10V$
Gate-source charge	Q_{gs}^*	-	0.7	-	nC	$V_{GS} = 4.5V, R_L = 4\Omega$
Gate-drain charge	Q_{gd}^*	-	0.6	-	nC	$R_G = 10\Omega$

*Pulsed

● **Body diode characteristics** (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V_{SD}^*	-	-	1.2	V	$I_S = 2.5A, V_{GS} = 0V$

*Pulsed

● **Electrical characteristics** (Ta = 25°C)

<Tr2(Pch)>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	± 10	μA	$V_{GS} = \pm 10V, V_{DS} = 0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	-20	-	-	V	$I_D = -1mA, V_{GS} = 0V$
Zero gate voltage drain current	I_{DSS}		-	-1	μA	$V_{DS} = -20V, V_{GS} = 0V$
Gate threshold voltage	$V_{GS(th)}$	-0.3	-	-1.0	V	$V_{DS} = -10V, I_D = -1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	-	49	68	m Ω	$I_D = -2.5A, V_{GS} = -4.5V$
		-	68	95		$I_D = -1.2A, V_{GS} = -2.5V$
			100	150		$I_D = -1.2A, V_{GS} = -1.8V$
		-	140	280		$I_D = -0.5A, V_{GS} = -1.5V$
Forward transfer admittance	$ Y_{fs} ^*$	2.5	-	-	S	$V_{DS} = -10V, I_D = -2.5A$
Input capacitance	C_{iss}	-	1270	-	pF	$V_{DS} = -10V$
Output capacitance	C_{oss}	-	100	-	pF	$V_{GS} = 0V$
Reverse transfer capacitance	C_{rss}	-	90	-	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}^*$	-	9	-	ns	$I_D = -1.2A, V_{DD} = -10V$
Rise time	t_r^*	-	30	-	ns	$V_{GS} = -4.5V$
Turn-off delay time	$t_{d(off)}^*$	-	120	-	ns	$R_L = 8.3\Omega$
Fall time	t_f^*	-	85	-	ns	$R_G = 10\Omega$
Total gate charge	Q_g^*	-	12	-	nC	$I_D = -2.5A, V_{DD} = -10V$
Gate-source charge	Q_{gs}^*	-	2.5	-	nC	$V_{GS} = -4.5V, R_L = 4\Omega$
Gate-drain charge	Q_{gd}^*	-	2	-	nC	$R_G = 10\Omega$

*Pulsed

● **Body diode characteristics** (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V_{SD}^*	-	-	-1.2	V	$I_s = -2.5A, V_{GS} = 0V$

*Pulsed

● Electrical characteristic curves (Ta = 25°C)

<Tr1(Nch)>

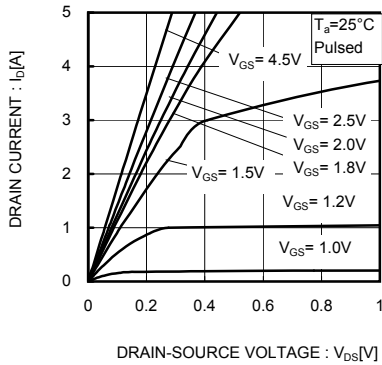


Fig.1 Typical Output Characteristics(I)

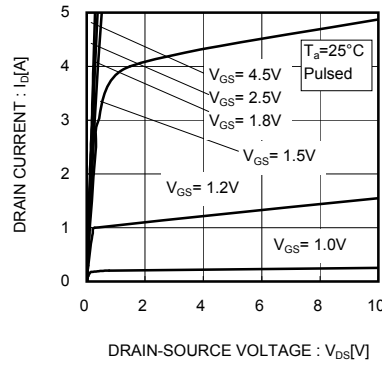


Fig.2 Typical Output Characteristics(II)

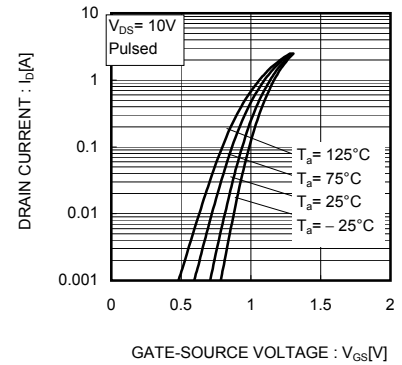


Fig.3 Typical Transfer Characteristics

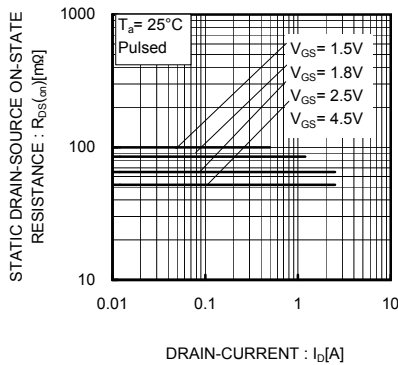


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(I)

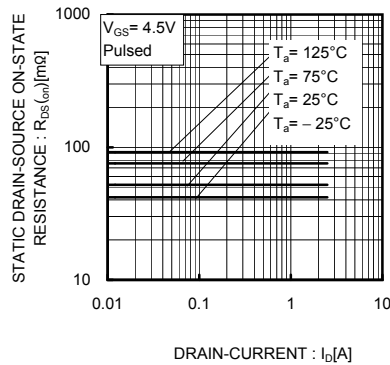


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(II)

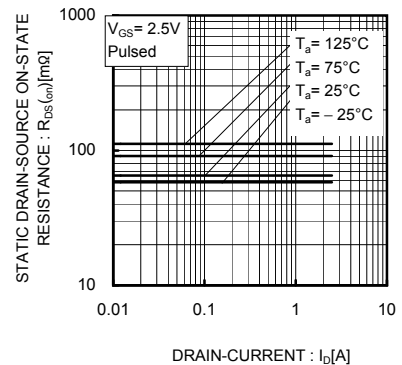


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(III)

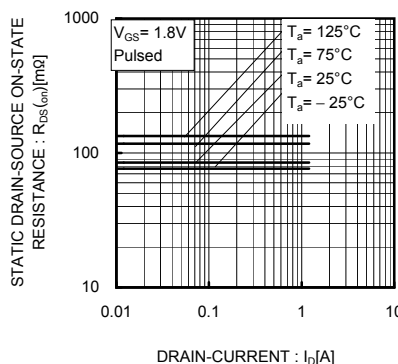


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(IV)

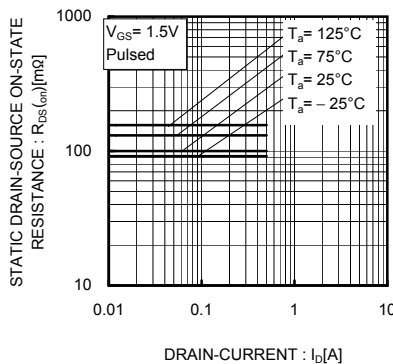


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current(V)

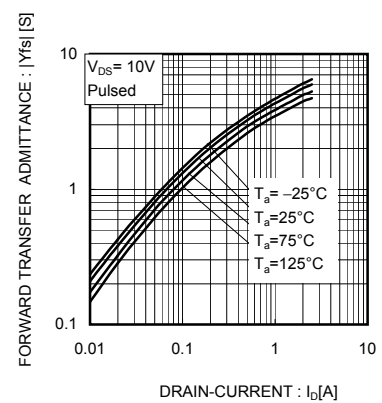


Fig.9 Forward Transfer Admittance vs. Drain Current

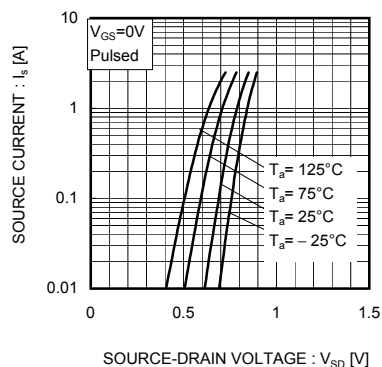


Fig.10 Reverse Drain Current
vs. Source-Drain Voltage

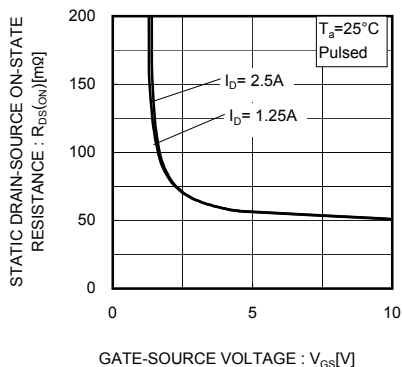


Fig.11 Static Drain-Source On-State
Resistance vs. Gate Source Voltage

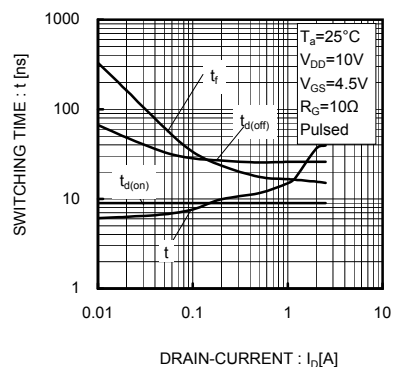


Fig.12 Switching Characteristics

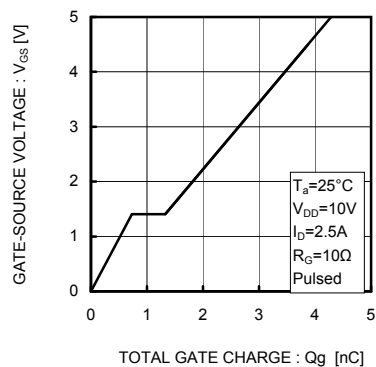


Fig.13 Dynamic Input Characteristics

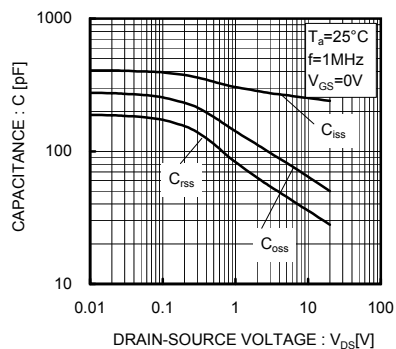


Fig.14 Typical Capacitance
vs. Drain-Source Voltage

<Tr2(Pch)>

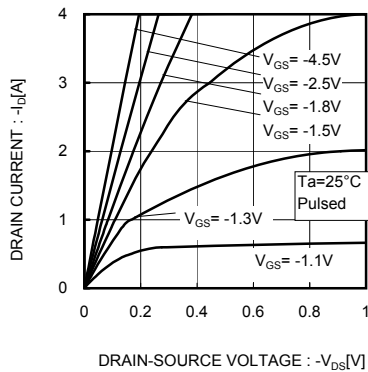


Fig.1 Typical Output Characteristics()

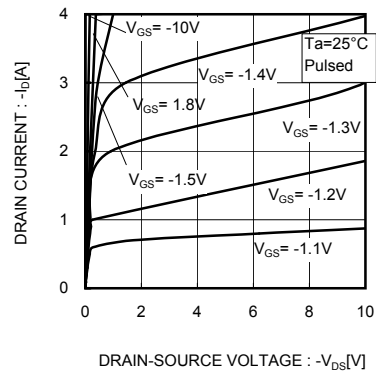


Fig.2 Typical Output Characteristics()

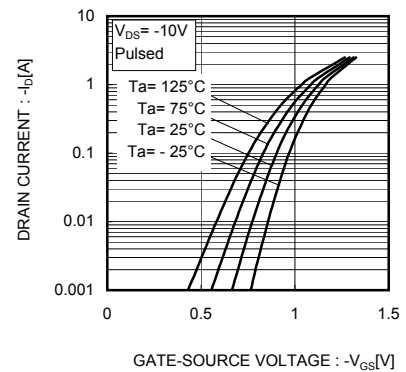


Fig.3 Typical Transfer Characteristics

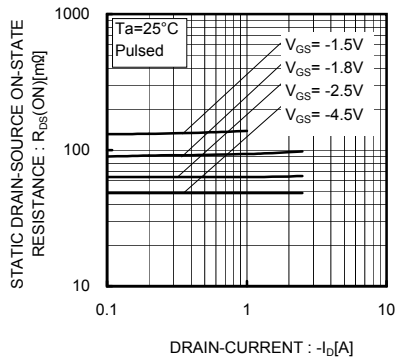


Fig.4 Static Drain-Source On-State Resistance vs. Drain

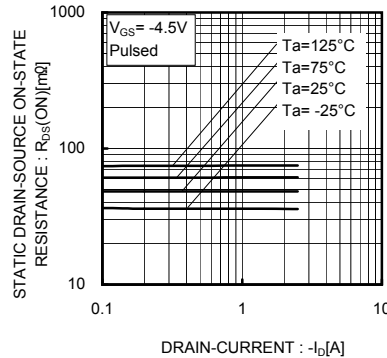


Fig.5 Static Drain-Source On-State Resistance vs. Drain

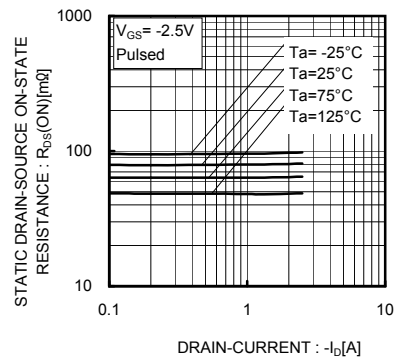


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current()

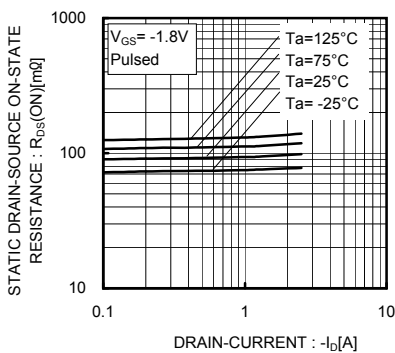


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current()

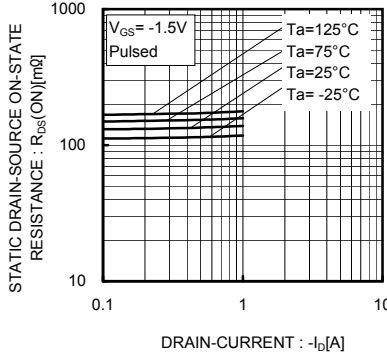


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current()

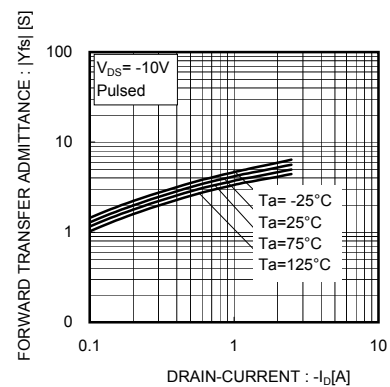


Fig.9 Forward Transfer Admittance vs. Drain Current

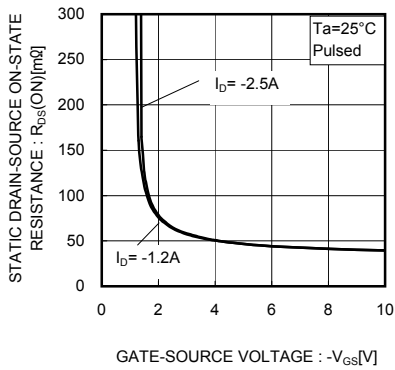


Fig.10 Static Drain-Source On-State Resistance vs. Gate Source Voltage

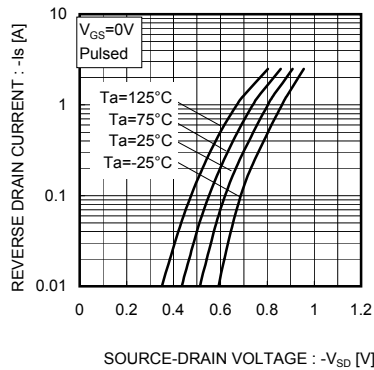


Fig.11 Reverse Drain Current vs. Source-Drain Voltage

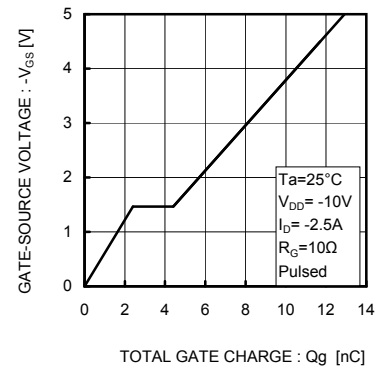


Fig.12 Dynamic Input Characteristics

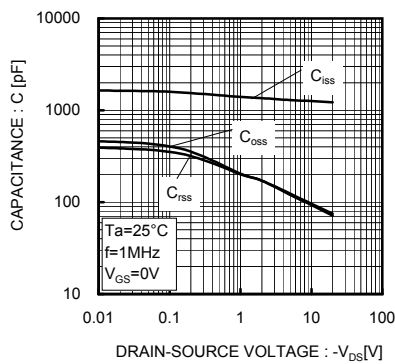


Fig.13 Typical Capacitance vs. Drain-Source

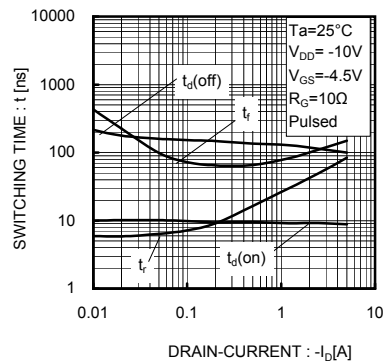


Fig.14 Switching Characteristics

● Measurement circuits

<Tr1(Nch)>

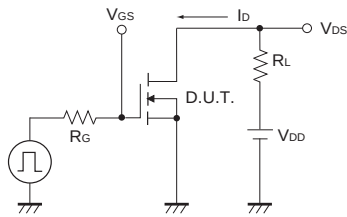


Fig.1-1 Switching time measurement circuit

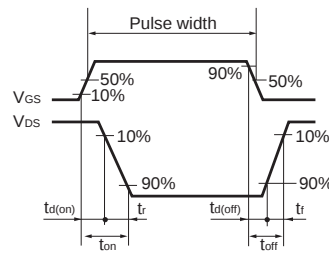


Fig.1-2 Switching waveforms

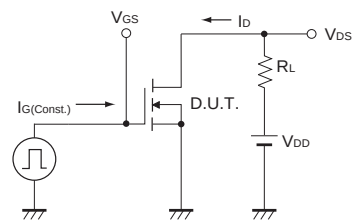


Fig.2-1 Gate charge measurement circuit

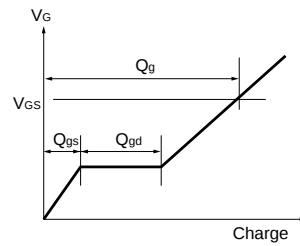


Fig.2-2 Gate Charge Waveform

<Tr2(Pch)>

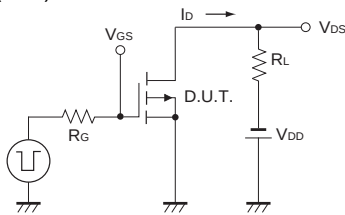


Fig.3-1 Switching time measurement circuit

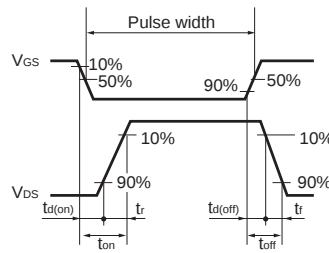


Fig.3-2 Switching waveforms

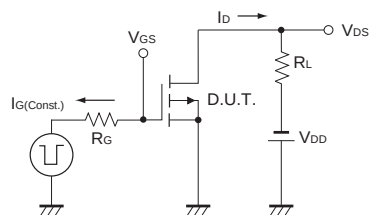


Fig.4-1 Gate charge measurement circuit

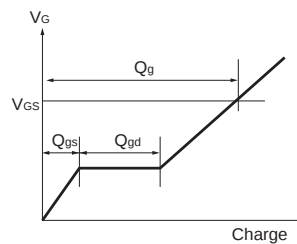


Fig.4-2 Gate charge waveform

● Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

Notes

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